

# Atsushi Tsurumaki-Fukuchi

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/8392296/publications.pdf>

Version: 2024-02-01

45  
papers

505  
citations

933264

10  
h-index

677027

22  
g-index

45  
all docs

45  
docs citations

45  
times ranked

987  
citing authors

#	ARTICLE	IF	CITATIONS
1	Impact of Bi Deficiencies on Ferroelectric Resistive Switching Characteristics Observed at p-Type Schottky-Like Pt/Bi <sub>1-x</sub> FeO <sub>3</sub> Interfaces. <i>Advanced Functional Materials</i> , 2012, 22, 1040-1047.	7.8	173
2	Switching operation and degradation of resistive random access memory composed of tungsten oxide and copper investigated using in-situ TEM. <i>Scientific Reports</i> , 2015, 5, 17103.	1.6	60
3	Resistive switching artificially induced in a dielectric/ferroelectric composite diode. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	51
4	Strong Surface Termination Effect on Electroresistance in Ferroelectric Tunnel Junctions. <i>Advanced Functional Materials</i> , 2015, 25, 2708-2714.	7.8	44
5	Probing electrochemistry at the nanoscale: in situ TEM and STM characterizations of conducting filaments in memristive devices. <i>Journal of Electroceramics</i> , 2017, 39, 73-93.	0.8	28
6	Smooth Interfacial Scavenging for Resistive Switching Oxide via the Formation of Highly Uniform Layers of Amorphous TaO <sub>x</sub> . <i>ACS Applied Materials &amp; Interfaces</i> , 2018, 10, 5609-5617.	4.0	22
7	Multilevel recording in Bi-deficient Pt/BFO/SRO heterostructures based on ferroelectric resistive switching targeting high-density information storage in nonvolatile memories. <i>Applied Physics Letters</i> , 2013, 103, .	1.5	20
8	Microstructural transitions in resistive random access memory composed of molybdenum oxide with copper during switching cycles. <i>Nanoscale</i> , 2016, 8, 14754-14766.	2.8	17
9	Modeling of hysteretic Schottky diode-like conduction in Pt/BiFeO <sub>3</sub> /SrRuO <sub>3</sub> switches. <i>Applied Physics Letters</i> , 2014, 105, .	1.5	13
10	Ca doping dependence of resistive switching characteristics in ferroelectric capacitors comprising Ca-doped BiFeO <sub>3</sub> . <i>Journal of Applied Physics</i> , 2015, 118, .	1.1	11
11	Periodic Coulomb blockade oscillations observed in single-layered Fe nanodot array. <i>Thin Solid Films</i> , 2020, 704, 138012.	0.8	7
12	Stable and Tunable Current-Induced Phase Transition in Epitaxial Thin Films of Ca <sub>2</sub> RuO <sub>4</sub> . <i>ACS Applied Materials &amp; Interfaces</i> , 2020, 12, 28368-28374.	4.0	7
13	Resistive switching characteristics in dielectric/ferroelectric composite devices improved by post-thermal annealing at relatively low temperature. <i>Applied Physics Letters</i> , 2014, 104, .	1.5	6
14	Fabrication and single-electron-transfer operation of a triple-dot single-electron transistor. <i>Journal of Applied Physics</i> , 2015, 118, .	1.1	6
15	Fabrication and evaluation of series-triple quantum dots by thermal oxidation of silicon nanowire. <i>AIP Advances</i> , 2015, 5, .	0.6	6
16	Observation of Conductive Filament in CBRAM at Switching Moment. <i>ECS Transactions</i> , 2017, 80, 895-902.	0.3	6
17	Initial states and analog switching behaviors of two major tantalum oxide resistive memories. <i>Japanese Journal of Applied Physics</i> , 2020, 59, 044004.	0.8	4
18	Charge-offset stability of single-electron devices based on single-layered Fe nanodot array. <i>AIP Advances</i> , 2021, 11, .	0.6	4

#	ARTICLE	IF	CITATIONS
19	Resistive Switching Memory Based on Ferroelectric Polarization Reversal at Schottky-like BiFeO <sub>3</sub> Interfaces. Materials Research Society Symposia Proceedings, 2012, 1430, 31.	0.1	3
20	Filamentary switching of ReRAM investigated by in-situ TEM. Japanese Journal of Applied Physics, 2020, 59, SG0803.	0.8	3
21	Capacitance evaluation of compact silicon triple quantum dots by simultaneous gate voltage sweeping. Journal of Applied Physics, 2016, 120, 234502.	1.1	2
22	Analog memory characteristics of 1T1R MoO <sub>x</sub> resistive random access memory. , 2016, , .		2
23	In-situ Electron Microscopy of Cu Movement in MoO <sub>x</sub> /Al <sub>2</sub> O <sub>3</sub> Bilayer CBRAM during Cyclic Switching. ECS Transactions, 2017, 80, 903-910.	0.3	2
24	Oxygen Distribution around Filament in Ta-O Resistive RAM Fabricated Using 40 nm CMOS Technology. , 2018, , .		2
25	Tunnel magnetocapacitance in Fe/MgF <sub>2</sub> single nanogranular layered films. Applied Physics Letters, 2020, 116, .	1.5	2
26	EELS Analysis of Oxygen Scavenging Effect in a Resistive Switching Structure of Pt/Ta/SrTiO <sub>3</sub> /Pt. MRS Advances, 2018, 3, 1925-1930.	0.5	1
27	Controlled Current Transport in Pt/Nb:SrTiO <sub>3</sub> Junctions via Insertion of Uniform Thin Layers of TaO <sub>x</sub> . Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900136.	1.2	1
28	Initial electrical properties of tantalum oxide resistive memories influenced by oxygen defect concentrations. Japanese Journal of Applied Physics, 2021, 60, SCCE03.	0.8	1
29	In-situ TEM of Nanoscale ReRAM Devices. Vacuum and Surface Science, 2018, 61, 766-771.	0.0	1
30	Superconducting weak link generated on a linear array of substrate steps in ultrathin films of $YBa_2Cu_3O_{7-x}$ . Physical Review B, 2009, 80, .	1.1	0
31	Superconducting weak link generated at atomic steps on a substrate in a $YBa_2Cu_3O_{7-x}$ film. Physica C: Superconductivity and Its Applications, 2010, 470, S863-S864.	0.6	0
32	Modeling of the I-V and I-t characteristics of multiferroic BiFeO <sub>3</sub> layers. , 2015, , .		0
33	Study on lateral ReRAM by the use of in-situ TEM. , 2016, , .		0
34	Evaluation of the origin of excited states appeared in small Si single-electron transistors. , 2016, , .		0
35	Evaluation of serially coupled triple quantum dots with a compact device structure by a simultaneous voltage-sweeping method. , 2016, , .		0
36	(Invited) Evaluation of Coupled Triple Quantum Dots with Compact Device Structure. ECS Transactions, 2017, 80, 173-180.	0.3	0

#	ARTICLE	IF	CITATIONS
37	Evaluation of multilevel memory capability of ReRAM using TaO <sub>2</sub> /O <sub>5</sub> insulator and different electrode materials. , 2017, , .		0
38	EELS Analysis of Oxygen Scavenging Effect in a Resistive Switching Structure of Pt/Ta/SrTiO <sub>3</sub> /Pt “CORRIGENDUM. MRS Advances, 2018, 3, 2075-2075.	0.5	0
39	Nanoscale Switching and Degradation of Resistive Random Access Memory Studied by In Situ Electron Microscopy. , 0, , .		0
40	Switching Current of Ta <sub>2</sub> O <sub>5</sub> -Based Resistive Analog Memories. , 2019, , .		0
41	Double-gate single-electron devices formed by single-layered Fe nanodot array. , 2020, , .		0
42	Initialization process of Cu-based WO <sub>x</sub> conductive bridge RAM investigated via in situ transmission electron microscopy. Japanese Journal of Applied Physics, 2020, 59, S1E01.	0.8	0
43	(Invited) Nanoscale Probing of Field-Driven Ion Migration in TaO <sub>x</sub> for Neuromorphic Memristor Applications. ECS Transactions, 2021, 104, 93-101.	0.3	0
44	Probing Electrochemistry at the Nanoscale: In Situ TEM and STM Characterizations of Conducting Filaments in Memristive Devices. Kluwer International Series in Electronic Materials: Science and Technology, 2022, , 87-120.	0.3	0
45	(Invited) Nanoscale Probing of Field-Driven Ion Migration in TaO <sub>x</sub> for Neuromorphic Memristor Applications. ECS Meeting Abstracts, 2021, MA2021-02, 922-922.	0.0	0